Panasonic

MOS FET FC4B21320L1

FC4B21320L1 Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

Features

- Source-source ON resistance:Rss(on) typ. = $39 \text{ m}\Omega(\text{VGS} = 3.8 \text{ V})$
- CSP(Chip Size Package)
- · RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 2D

Packaging

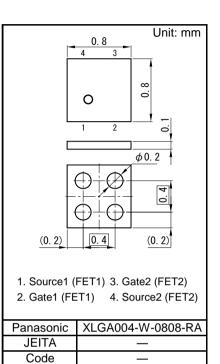
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

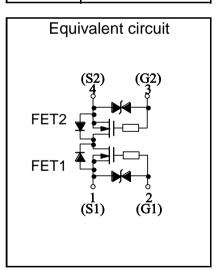
■ Absolute Maximum Ratings Ta = 25 °C							
Parameter	Symbol	Rating	Unit				
Source-source Voltage	VSS	12	V				
Gate-source Voltage	VGS	±8	V				
Source Current (DC)	IS *1	2.5	A				
	IS *2	4	А				
Source Current (Pulsed)	ISp *3	25	А				
Total Power Dissipation	PD ^{*1}	0.34	W				
	PD ^{*2}	0.9	W				
Channel Temperature	Tch	150	°C				
Storage Temperature Range	Tstg	-55 to +150	°C				
Thermal Resistance (ch-a)	Rth ^{*1}	368	°C/W				
	Rth ^{*2}	139	°C/W				

Note *1 Mounted on FR4 board ($25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$) using the minimum recommended pad size ($36\mu \text{m}$ Copper).

*2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).

*3 t = 10 μ s, Duty Cycle \leq 1 %







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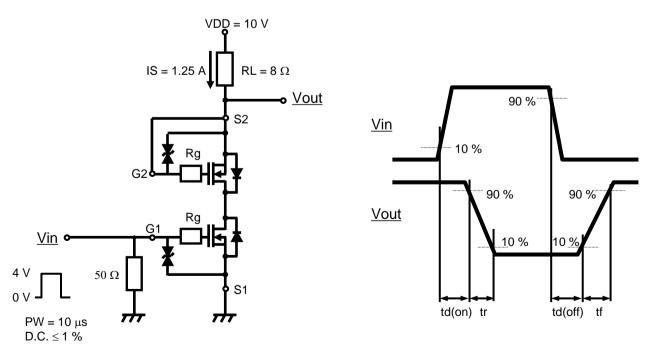
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V	
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μA	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 V, VSS = 0 V$			±10		
	1655	$VGS = \pm 5 V, VSS = 0 V$			±1.0	μA	
Gate-source Threshold Voltage	Vth	IS = 0.07 mA, VSS = 10 V	0.35	0.9	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 1.25 A, VGS = 4.5 V	27	36	48	mΩ	
	RSS(on)2	IS = 1.25 A, VGS = 3.8 V	29	39	53		
	RSS(on)3	IS = 1.25 A, VGS = 3.1 V	32	45	75		
	RSS(on)4	IS = 1.25 A, VGS = 2.5 V	35	58	115		
Body Diode Forward Voltage	VF(s-s)	IF = 1.25 A, VGS = 0 V		0.6	1.2	V	
Input Capacitance ^{*1}	Ciss			205			
Output Capacitance ^{*1}	Coss	VSS = 10 V, VGS = 0 V, f = 1 MHz		50		pF	
Reverse Transfer Capacitance ^{*1}	Crss			40			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.10		μS	
Rise Time ^{*1,*2}	tr	IS = 1.25 A		0.15			
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		0.50		μS	
Fall Time ^{*1,*2}	tf	IS = 1.25 A		0.30			
Total Gate Charge ^{*1}	Qg	VDD = 10 V		3.5			
Gate-source Charge ^{*1}	Qgs	VGS = 0 to 4.0 V,		0.8		nC	
Gate-drain Charge ^{*1}	Qgd	IS = 1.25 A		1.0			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

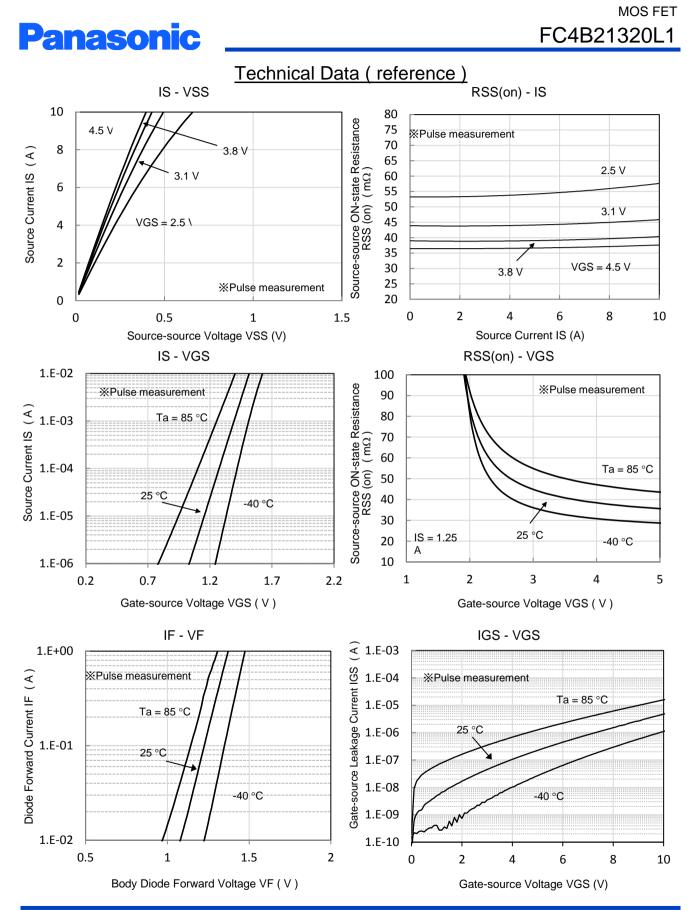
*1 Guaranteed by design, not subject to production testing

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

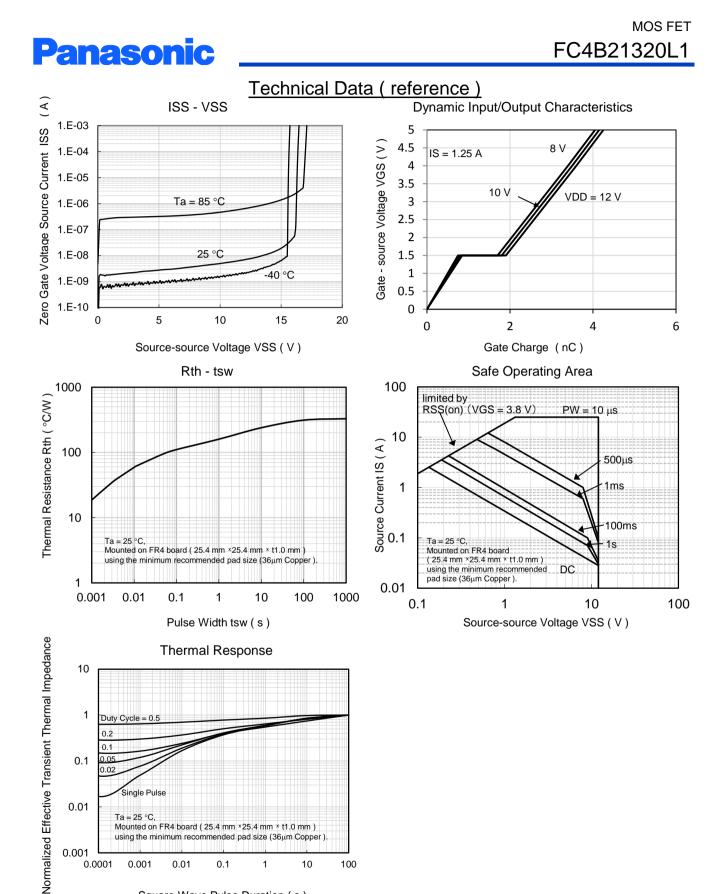


Note2 : Measurement circuit

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Square Wave Pulse Duration (s)

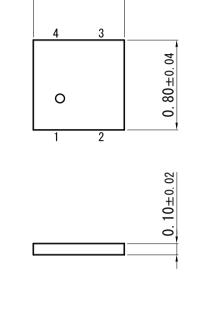
Doc No. TT4-EA-15079 Revision. 1



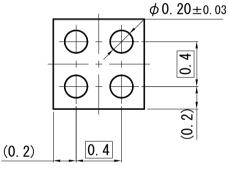
Outline (XLGA004-W-0808-RA)

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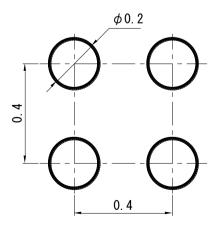
Unit: mm



 0.80 ± 0.04



■ Land Pattern (Reference)



Unit: mm

Established : 2015-10-23 Revised : ###-##-##

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